

# High Temperature CVD system

## CVD system for SiC (HTC3100)



CVD system for SiC (HTC3100), supplied to National Institute of Advanced Industrial Science and Technology

- Reactor : Vertical type, Made of quartz  
Face down
- Load-lock system : With transfer rod
- Substrate size :  $1 \times \phi 3"$
- Substrate heating : RF heating type
- Maximum heating : 1800°C(Pyrometer value)  
temperature
- Applications : SiC, etc.

## All-in-one CVD system



All-In-One CVD system supplied to Nara Institute of Science and Technology

- Reactor : Horizontal type, Made of quartz
- Substrate size :  $1 \times \phi 2"$
- Substrate heating : RF heating type
- Maximum heating : 1500°C(Pyrometer value)  
temperature
- Foot print : 1.3m  $\times$  1.3m
- Applications : SiC, etc.

## Ultra High Temperature CVD system (SH2001-HTA)

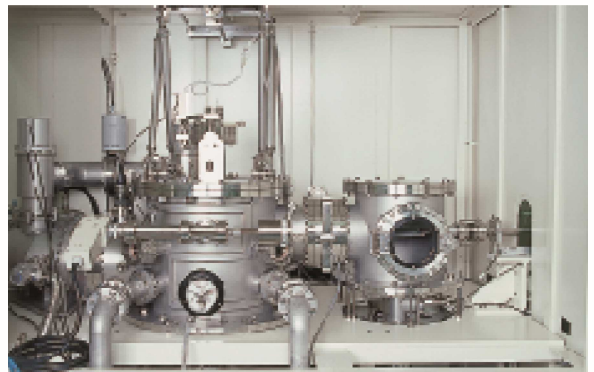


Ultra High Temperature CVD system (SH2001-HTA) supplied to Meijo University

- Reactor : Horizontal type, Made of stainless steel  
Face down
- Substrate size :  $1 \times \phi 1"$
- Substrate heating : Resistance heating type
- Maximum heating : 1800°C  
temperature (T.C. Value for control)
- Applications : AlN, etc.

Patent pending

## High Temperature CVD system / Oxidation system (OV4001)



- Reactor : Vertical type, Made of stainless steel
- Substrate size :  $1 \times \phi 4"$
- Substrate heating : Resistance heating type
- Maximum heating : 1400°C (T.C. Value for control)  
temperature
- Applications : Oxidation for SiC, etc.

Patent awarded